Con. 5552 -13

F.E SemI ((BGS)) APP Physics

GX-10030

## (Revised Course)

(2 Hours)

[Total Marks: 60

N.B.: (1) Question No.1 is co	ompulsary.
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- (2) Attempt any three questions from Question No. 2 to 6.
- (2) Use suitale data wherever required.
- (3) Figures to the right indicate full marks.

## 1. Solve any five from the following:-

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- (a) Define the term space lattice, unit cell and lattice parameter.
- (b) Find the interplaner spacing between the family of planes (111) in a crystal of lattice constant 3A°.
- (c) Represent the following in the cubic unit cell:-(1T2), (002), [121]
- (d) Define drift current, diffusion current and mobility of charge carriers.
- (e) Explain the use of P-N junction as a solar cell.
- (f) State with neat diagram direct and inverse Piezoelectric effect.
- (g) What is magnetic circuit? Explain Ohm's Law in case of magnetic circuit.
- (a) Explain the Hall effect in metal? Derive the formulae to determine the density
  and mobility of the electrons.
  - (b) Define ligeancy and critical radius ratio in case of ionic solid. Write the conditions for stability of ionic crystal in 3-D? Determine critical radius ratio for ligancy 6.
- 3. (a) Explain with neat diagram construction of Bragg's X-ray spectrometer? Write the procedure to determine crystal structure. Calculate the maximum order of diffraction if X-rays of wavelength 0.819 A° is incident on a crystal of lattice spacing 0.282 nm.
  - (b) Calculate the number of turns required to produce a magnetic flux of 4 x  $10^5$  wb, if an iron rod of length 50 cm and cross sectional area 4 cm<sup>2</sup> carrying an electric current 1A is in the form of ring. (Permeability of iron is  $65 \times 10^{-4}$  H/m).
- 4. (a) What is mesomorphic state of matter? Explain with neat diagram cholesteric phase. 5
  - (b) What is dielectric polarization and dielectric susceptibility? Find the relation 5 between them?

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- (c) The resistivity of intrinsic InSb at room termperatrue is  $2 \times 10^{-4} \Omega$  cm. If the mobility of electron is  $6 \text{ m}^2/\text{V}$ -sec and mobility of hole is  $0.2 \text{ m}^2/\text{V}$ -sec. Calculate its instrinsic carrier dentsity.
- 5. (a) Identify the crystal structure if its density is 9.6 x 10<sup>2</sup> kg/m<sup>3</sup>, lattice constant is 5 4.3 A° and atomic weight is 23.
  - (b) Explain the formation of depletion region in P-N junction.
  - (c) Define reverberation time? State Sabine's formula and explain the terms involved 5 in it?
- 6. (a) What are soft and Hard magnetic material? State their properties and applications. 5
  - (b) What is Fermi level in semiconductor? Show that in intrinsic semiconductor Fermi 5 level always at the middle between the forbidden energy gap?
  - (c) An Ultrasonic sound wave is used to detect the position of defect in a steel bar of thickness 50 cm. If the echo times are 40 and 90 μ-sec. Locate the position of defect.